μA726C

TEMPERATURE-CONTROLLED DIFFERENTIAL PAIR

FAIRCHILD LINEAR INTEGRATED CIRCUITS

GENERAL DESCRIPTION—The μA726C is a monolithic transistor pair in a high thermal-resistance package, held at a constant temperature by active temperature regulator circuitry. The transistor pair displays the excellent matching, close thermal coupling, and fast thermal response inherent in monolithic construction. The high gain and low standby dissipation of the regulator circuit permits tight temperature control over a wide range of ambient temperatures. It is intended for use as an input stage in very-low-drift dc amplifiers, replacing complex chopper-stabilized amplifiers; it is also useful as the nonlinear element in logarithmic amplifiers and multipliers where the highly predictable exponential relation between emitter-base voltage and collector current is employed. The device is constructed on a single silicon chip using the Fairchild Planar* process. For full temperature range (−55°C to +125°C) see μA726 data sheet.

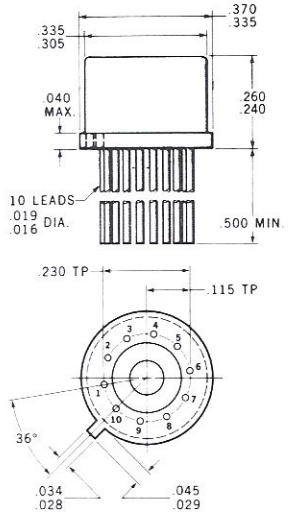
ABSOLUTE MAXIMUM RATINGS

Operating Temperature Range	0°C to +85°C
Storage Temperature Range	−65°C to +150°C
Lead Temperature (Soldering, 60 seconds)	300°C
Supply Voltage	±18V

MAXIMUM RATINGS FOR EACH TRANSISTOR

Maximum collector-to-substrate voltage	40V
BV_{CBO}	40V
LV_{CEO} (Note 1)	30V
BV_{EBO}	5V
Collector Current	5 mA

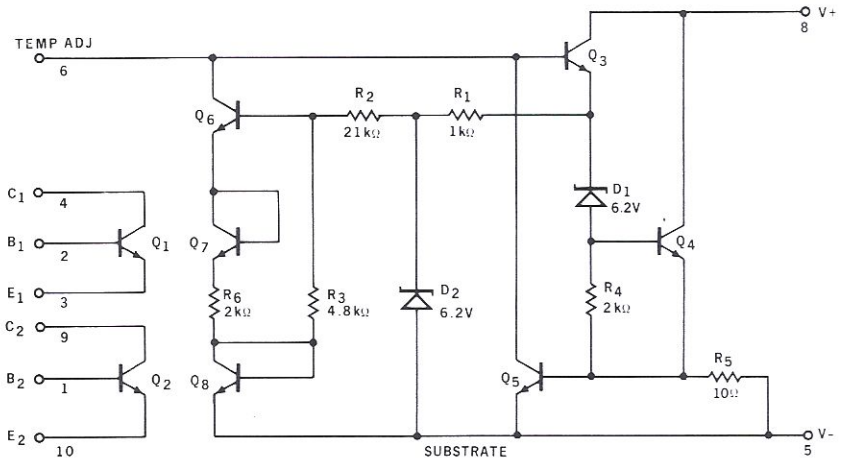
PHYSICAL DIMENSIONS



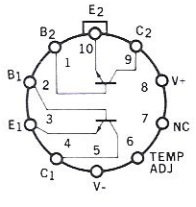
NOTES: All dimensions in inches
Leads are gold-plated Kovar
Package weight is 1.32 grams

ORDER PART NO. U5J772632X

SCHEMATIC DIAGRAM



CONNECTION DIAGRAM



TOP VIEW

NOTE: (1) Measured at 1 mA collector current.

*Planar is a patented Fairchild process.

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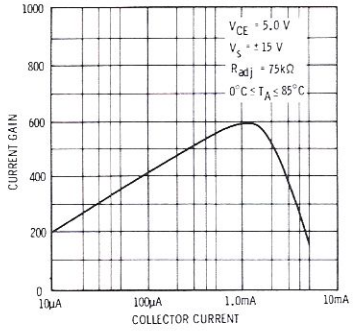
ELECTRICAL CHARACTERISTICS ($0°C \leq T_A \leq +85°C$, $V_S = \pm 15V$, $R_{adj} = 75\ k\Omega$ unless otherwise specified)

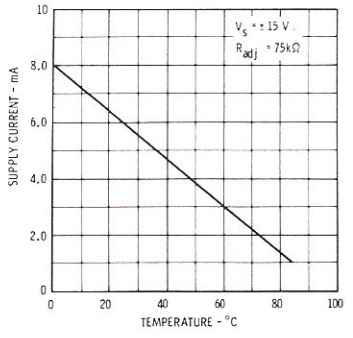
PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Input Offset Voltage	$10\ \mu A \leq I_C \leq 100\ \mu A$ $V_{CE} = 5V$, $R_S \leq 50\Omega$		1.0	3.0	mV
Input Offset Current	$I_C = 10\ \mu A$, $V_{CE} = 5V$		10	100	nA
Input Offset Current	$I_C = 100\ \mu A$, $V_{CE} = 5V$		50	400	nA
Average Input Bias Current	$I_C = 10\ \mu A$, $V_{CE} = 5V$		50	300	nA
Average Input Bias Current	$I_C = 100\ \mu A$, $V_{CE} = 5V$		250	1000	nA
Offset Voltage Change	$I_C = 10\ \mu A$, $5V \leq V_{CE} \leq 25V$, $R_S \leq 100\ k\Omega$		0.3	6.0	mV
Offset Voltage Change	$I_C = 100\ \mu A$, $5V \leq V_{CE} \leq 25V$, $R_S \leq 10\ k\Omega$		0.3	6.0	mV
Input Offset Voltage Drift	$I_C = 100\ \mu A$, $V_{CE} = 5V$, $R_S \leq 50\Omega$		0.2	2.0	μV/°C
Input Offset Current Drift	$I_C = 10\ \mu A$, $V_{CE} = 5V$		10		pA/°C
Input Offset Current Drift	$I_C = 100\ \mu A$, $V_{CE} = 5V$		30		pA/°C
Supply Voltage Rejection Ratio	$I_C = 100\ \mu A$, $R_S = 50\Omega$		25		μV/V
Low-Frequency Noise	$I_C = 10\ \mu A$, $V_{CE} = 5V$, $R_S \leq 50\Omega$, BW = 0.001 Hz to 0.1 Hz		4.0		μV pp
Broadband Noise	$I_C = 10\ \mu A$, $V_{CE} = 5V$, $R_S \leq 50\Omega$, BW = 0.1 Hz to 10 kHz		10		μV pp
Long-Term Drift	$I_C = 100\ \mu A$, $V_{CE} = 5V$, $R_S \leq 50\Omega$, $T_A = 25°C$		5.0		μV/week
High-Frequency Current Gain	f = 20 MHz, $I_C = 100\ \mu A$, $V_{CE} = 5V$	1.5	3.5		
Output Capacitance	$I_E = 0$, $V_{CB} = 5V$		1.0		pF
Emitter Transition Capacitance	$I_E = 100\ \mu A$		1.0		pF
Collector Saturation Voltage	$I_B = 100\ \mu A$, $I_C = 1\ mA$		0.5	1.0	V

TYPICAL PERFORMANCE CURVES

CURRENT GAIN AS A FUNCTION OF COLLECTOR CURRENT



SUPPLY CURRENT AS A FUNCTION OF AMBIENT TEMPERATURE



TYPICAL X1000 CIRCUIT